

Standard Rectifier

 V_{RRM} 1200 V =

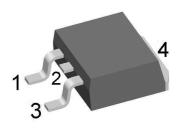
30 A

 V_{F} 1.25 V

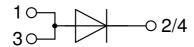
Single Diode

Part number

DSI30-12AS



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

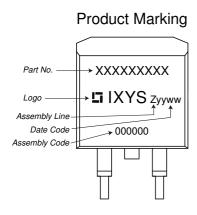


Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	cking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I _R	reverse current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			40	μΑ
		$V_R = 1200 \text{ V}$	$T_{VJ} = 150$ °C			1.5	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			1.29	V
		$I_F = 60 \text{ A}$				1.60	٧
		I _F = 30 A	T _{VJ} = 150 °C			1.25	٧
		$I_F = 60 \text{ A}$				1.66	٧
I FAV	average forward current	T _C = 130°C	$T_{VJ} = 175$ °C			30	Α
		rectangular d = 0.5					i
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.82	٧
r _F	slope resistance \(\) for power	loss calculation only				14.1	mΩ
R _{thJC}	thermal resistance junction to ca	ase				0.9	K/W
R _{thCH}	thermal resistance case to heats	sink			0.25		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			160	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			300	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			325	Α
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			255	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			275	Α
l ²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			450	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			440	A²s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			325	A²s
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			315	A²s
CJ	junction capacitance	$V_{R} = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		10		pF



Package TO-263 (D2Pak)				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal 1)			35	Α	
T _{VJ}	virtual junction temperature		-40		175	°C	
T _{op}	operation temperature		-40		150	°C	
T _{stg}	storage temperature		-40		150	°C	
Weight				2		g	
F _c	mounting force with clip		20		60	N	

¹⁾ l_{nusc} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.



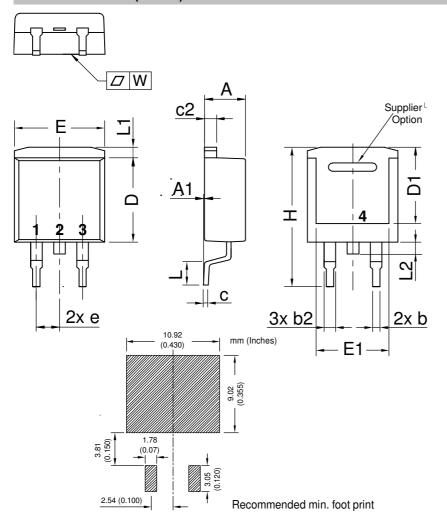
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSI30-12AS	DSI30-12AS	Tape & Reel	800	507511
Alternative	DSI30-12AS-TUB	DSI30-12AS	Tube	50	470988

Similar Part	Package	Voltage class
DSI30-12A	TO-220AC (2)	1200
DSI30-12AC	ISOPLUS220AC (2)	1200
DSI30-16AS	TO-263AB (D2Pak) (2)	1600
DSI30-16A	TO-220AC (2)	1600
DSI30-08AS	TO-263AB (D2Pak) (2)	800
DSI30-08A	TO-220AC (2)	800
DSI30-08AC	ISOPLUS220AC (2)	800

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 175 ^{\circ}\text{C}$
$I \rightarrow V_0$)—[R _o]-	Rectifier		
V _{0 max}	threshold voltage	0.82		V
$R_{0\;max}$	slope resistance *	11		$m\Omega$

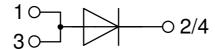


Outlines TO-263 (D2Pak)



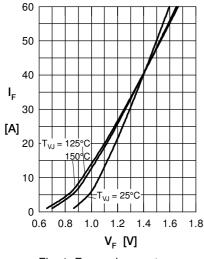
	Millimeter		Inches		
Dim.	min	max	min	max	
Α	4.06	4.83	0.160	0.190	
A1	typ.	0.10	typ. 0	0.004	
A2	2.		0.095		
b	0.51	0.99	0.020	0.039	
b2	1.14	1.40	0.045	0.055	
С	0.40	0.74	0.016	0.029	
c2	1.14	1.40	0.045	0.055	
D	8.38	9.40	0.330	0.370	
D1	8.00	8.89	0.315	0.350	
D2	2	.5	0.098		
Е	9.65	10.41	0.380	0.410	
E1	6.22	8.50	0.245	0.335	
е	2,54	BSC	0,100	0,100 BSC	
e1	4.28		0.169		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	1.02	1.68	0.040	0.066	
W	typ. 0.02	0.040	typ. 0.0008	0.002	

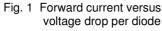
All dimensions conform with and/or within JEDEC standard.





Rectifier





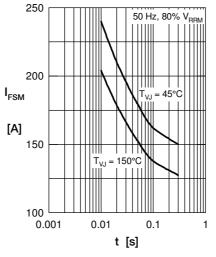


Fig. 2 Surge overload current

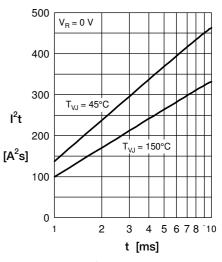


Fig. 3 I²t versus time per diode

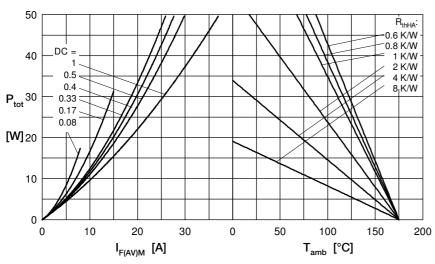


Fig. 4 Power dissipation vs. direct output current and ambient temperature

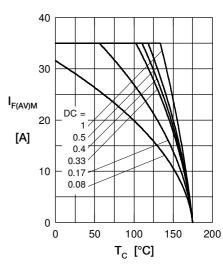


Fig. 5 Max. forward current vs. case temperature

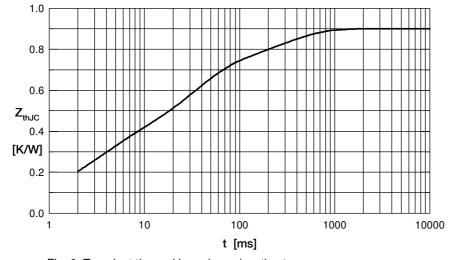


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.03	0.0004
2	0.08	0.002
3	0.2	0.003
4	0.39	0.03
5	0.2	0.29